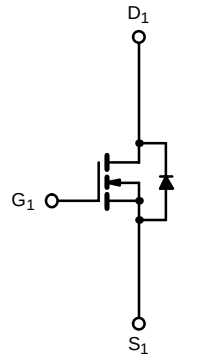
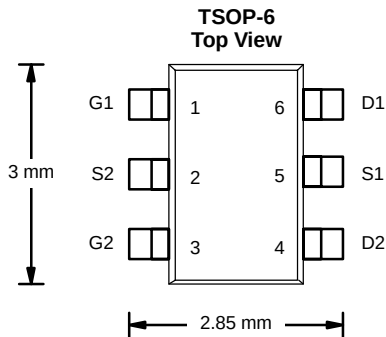




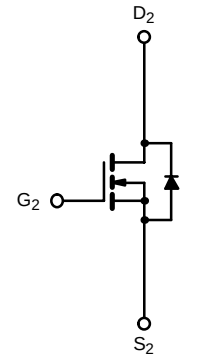
Dual N-Channel 20-V (D-S) MOSFET

TrenchFET®
Power MOSFETs

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.125 @ $V_{GS} = 4.5$ V	2.4
	0.200 @ $V_{GS} = 2.5$ V	1.8



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 sec	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V _{GS}	± 12		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	2.4	2.0	A
	T _A = 85°C		1.7	1.4	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	8		
Continuous Source Current (Diode Conduction) ^a		I _S	1.05	0.75	W
Maximum Power Dissipation ^a	T _A = 25°C	P _D	1.15	0.83	
	T _A = 85°C		0.59	0.53	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	–55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	93	110	$^\circ\text{C/W}$
	Steady State		130	150	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	75	90	

Notes

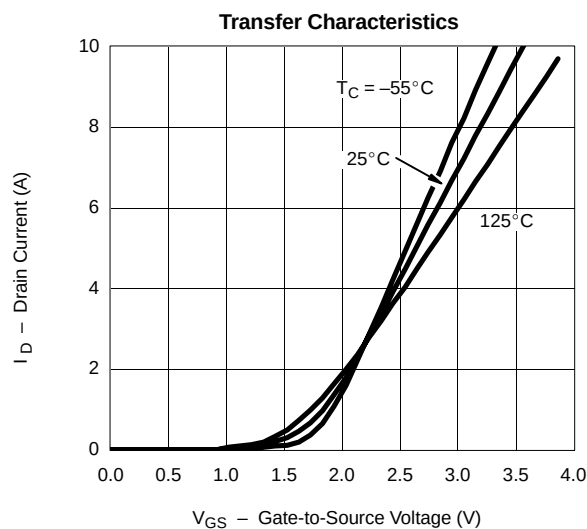
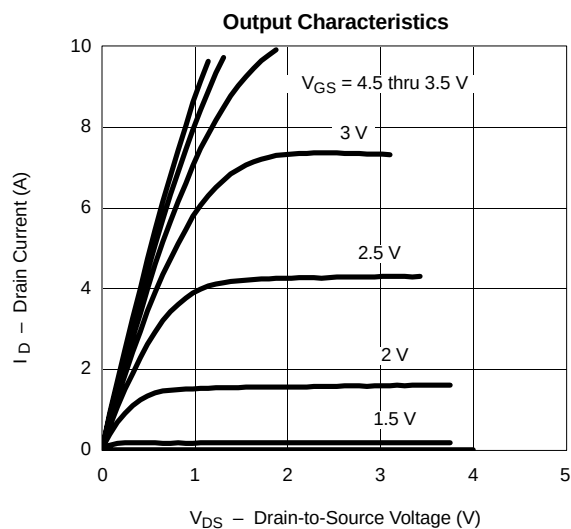
a. Surface Mounted on 1" x 1" FR4 Board.

SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.6			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 12\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 16\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 85^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 4.5\ \text{V}$	5			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\ \text{V}, I_D = 2.4\ \text{A}$		0.100	0.125	Ω
		$V_{GS} = 2.5\ \text{V}, I_D = 1.0\ \text{A}$		0.160	0.200	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 5\ \text{V}, I_D = 2.4\ \text{A}$		5		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.05\ \text{A}, V_{GS} = 0\ \text{V}$		0.79	1.10	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\ \text{V}, V_{GS} = 4.5\ \text{V}, I_D = 2.4\ \text{A}$		2.1	4.0	nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.4		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\ \text{V}, R_L = 10\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 4.5\ \text{V}, R_G = 6\ \Omega$		10	17	ns
Rise Time	t_r			30	50	
Turn-Off Delay Time	$t_{d(off)}$			14	25	
Fall Time	t_f			6	12	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 3.0\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		30	50	

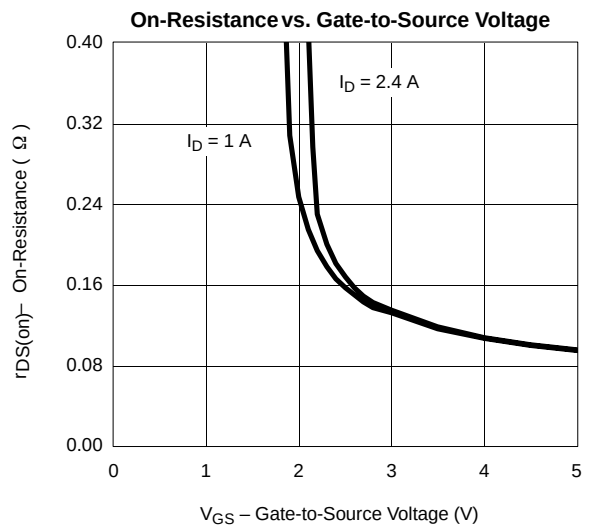
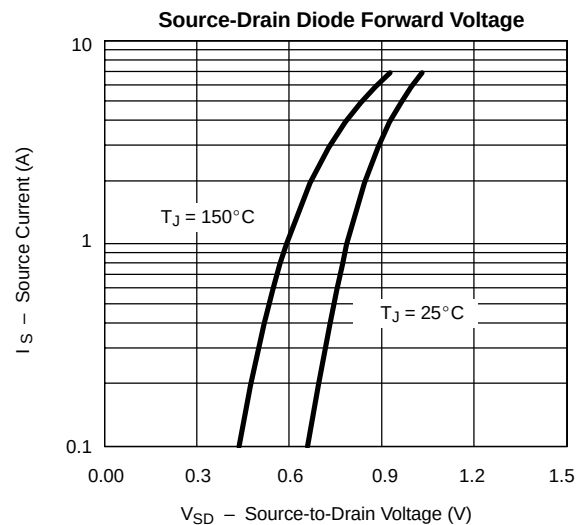
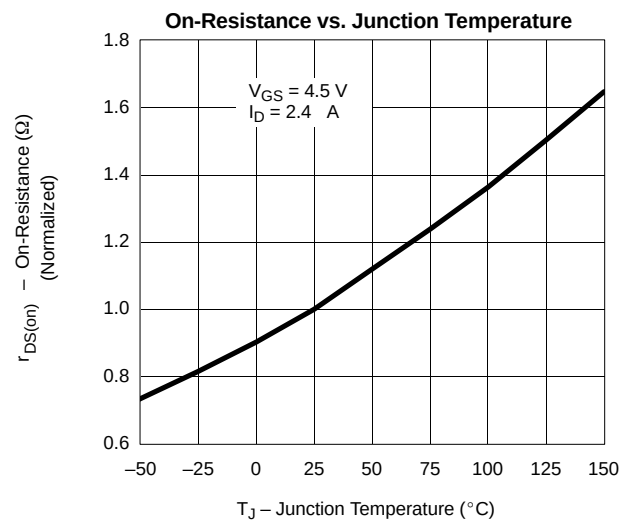
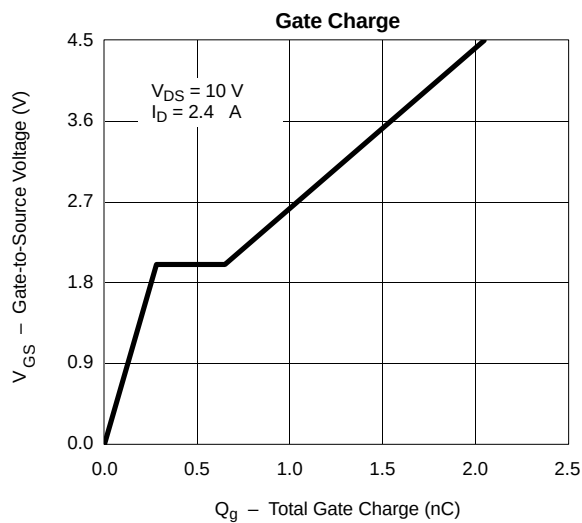
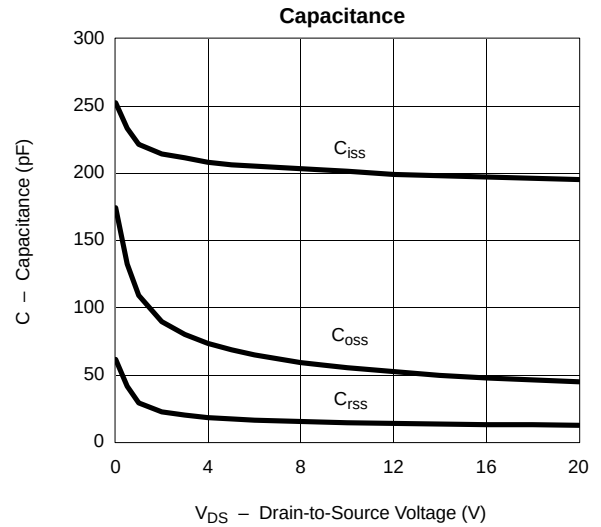
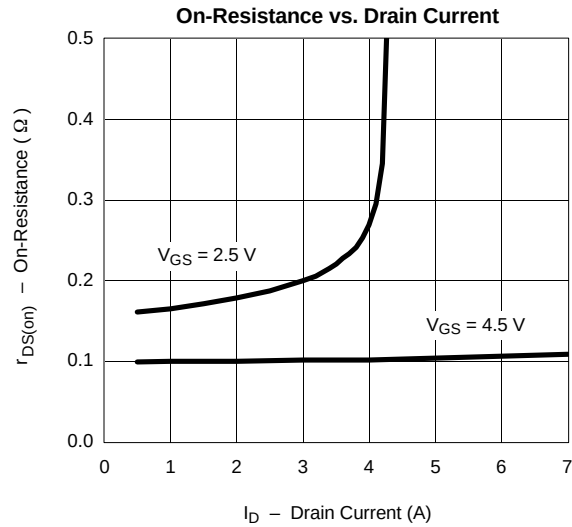
Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

